



# Bipolar NPN Bare Die – BTN995

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## Part Description

The BTN995 is a silicon BJT transistor available in bare die form and well suited for use in High Voltage Driver applications. PNP Complement is BTP995.

## Key Parameters:

- VCBO = 500V
- VCEO = 500V
- VEBO = 5V
- hFE = 150-300 @ VCE = 10V, IC = 0.001A
- VCE(Sat) = 0.5V @ IC = 0.05A, IB = 10mA
- fT = 50 MHz @ VCE = 20V, IE = 0A
- COBO = 8pF @ VCB = 20V

## Features

Designed to provide performance equivalent to NXP / NEXPERIA PMBTA45

## Die Size (Unawn)

850µm X 850µm, 33 Mils X 33 Mils

This is a shortform datasheet only

For the full datasheet

Please contact [sales@siliconsupplies.com](mailto:sales@siliconsupplies.com)

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